NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI PT9704** is Designed for wideband, large-signal amplifier Applications up to 500 MHz.

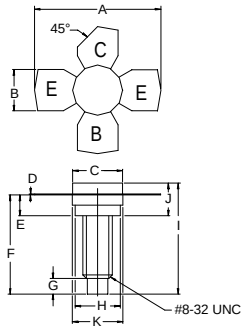
FEATURES INCLUDE:

- Gold Metalization
- Diffused Ballast Resistors
- Common Emitter

MAXIMUM RATINGS

I_C	5.0 A
V_{CE}	30 V
P_{DISS}	70 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	2.5 °C/W

PACKAGE STYLE .280" 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.055 / 26.80
B	.220 / 5.59	.230 /5.84
C	.270 / 6.86	.285 / 7.24
D	.003 / 0.08	.007 / 0.18
E	.117 / 2.97	.137 / 3.48
F	.572 / 14.53	
G	.130 / 3.30	
H	.245 / 6.22	.255 / 6.48
I	.640 / 16.26	
J	.175 / 4.45	.217 / 5.51
K	.275 / 6.99	.285 / 7.24

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I_C = 30 mA	30			V
BV_{CES}	I_C = 30 mA	60			V
BV_{EBO}	I_E = 3.0 mA	4.0			V
I_{CBO}	V_{CB} = 30 V			3.0	mA
h_{FE}	I_C = 100 mA V_{CE} = 5.0 V	10		150	---
C_{ob}	V_{CB} = 28 V f = 1.0 MHz			36	pF
G_{PE} η	V_{CE} = 28 V P_{OUT} = 30 W f = 400 MHz	7.0 60			dB %

ADVANCED SEMICONDUCTOR, INC.
7525 ETHEL AVENUE • NORTH HOLLYWOOD, CA 91605 • (818) 982-1200 • FAX (818) 765-3004

Specifications are subject to change without notice.